

**Vishay Siliconix** 

## Low-Voltage Single SPDT Analog Switch

### DESCRIPTION

The DG2714 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed ( $t_{ON}$ : 28 ns,  $t_{OFF}$ : 12 ns), low on-resistance ( $r_{DS(on)}$ : 0.85  $\Omega$ ) and small physical size (SC70), the DG2714 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2714 is built on Vishay Siliconix's low voltage submicron CMOS process. An epitaxial layer prevents latchup. Break-before -make is guaranteed for DG2714.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

### FEATURES

- Low Voltage Operation (1.6 V to 3.6 V)
- Low On-Resistance r<sub>DS(on)</sub>: 0.85 Ω Typ.
- Fast Switching t<sub>ON</sub>: 28 ns, t<sub>OFF</sub>: 12 ns
- Low Leakage
- TTL/CMOS Compatible
- 6-Pin SC-70 Package

#### **BENEFITS**

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

### **APPLICATIONS**

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: E8xx

TRUTH TABLE				
Logic	NC	NO		
0	ON	OFF		
1	OFF	ON		

ORDERING INFORMATION				
Temp Range	Package	Part Number		
- 40 to 85 °C	SC70-6	DG2714DL-T1 DG2714DL-T1-E3		

\* Pb containing terminations are not RoHS compliant, exemptions may apply



ROHS

COMPLIANT

# Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS						
Parameter	Limit	Unit				
Referenced V+ to GND	- 0.3 to + 4	v				
IN, COM, NC, NO <sup>a</sup>		- 0.3 to (V+ + 0.3)	V			
Continuous Current (NO, NC and COM Pins)		± 200	m (			
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 300	mA			
Storage Temperature (D Suffix)		- 65 to 150	°C			
Power Dissipation (Packages) <sup>b</sup>	6-Pin SO70 <sup>c</sup>	250	mW			

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate 3.1 mW/°C above 70 °C.

Parameter		Test Conditions Otherwise Unless Specified V+ = 1.8 V, ± 10 %, V <sub>IN</sub> = 0.4 or 1.1 V <sup>e</sup>	Temp <sup>a</sup>	Limits - 40 to 85 °C			
	Symbol			Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	Unit
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	V
On-Resistance	r <sub>ON</sub>	V+ = 1.8 V, V <sub>COM</sub> = 0.2 V/0.9 V I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room Full <sup>d</sup>		1.8	3.0 4.5	Ω
r <sub>ON</sub> Flatness <sup>d</sup>	r <sub>ON</sub> Flatness	V+ = 1.8 V, V <sub>COM</sub> = 0 to V+, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room			2	
r <sub>ON</sub> Match <sup>d</sup>	$\Delta r_{ON}$		Room			0.06	
	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	$V_{\rm NO}, V_{\rm NC} = 0.2 \text{ V/}2.0 \text{ V}, V_{\rm COM} = 2.0 \text{ V/}0.2 \text{ V}$	Room Full <sup>d</sup>	- 1 - 10		1 10	nA
Switch Off Leakage Current <sup>®</sup>	I <sub>COM(off)</sub>		Room Full <sup>d</sup>	- 1 - 10		1 10	
Channel-On Leakage Current <sup>f</sup>	I <sub>COM(on)</sub>	V+ = 2.2 V, V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 0.2 V/2.0 V	Room Full <sup>d</sup>	- 1 - 10		1 10	
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	1.1			V
Input Low Voltage	V <sub>INL</sub>		Full			0.4	
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		3.5		pF
Input Current <sup>f</sup>	$I_{\rm INL}$ or $I_{\rm INH}$	$V_{IN} = 0 \text{ or } V+$	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	$V_{NO}$ or $V_{NC}$ = 1.5 V, $R_L$ = 300 $\Omega,$ $C_L$ = 35 pF Figures 1 and 2	Room Full <sup>d</sup>		55	75 89	
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>		Room Full <sup>d</sup>		19	39 40	ns
Break-Before-Make Time <sup>d</sup>	t <sub>d</sub>		Room	3			
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$ , Figure 3	Room		13		рС
Off-Isolation <sup>d</sup>	OIRR	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 1 MHz	Room		- 64		dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 64		
NO, NC Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub> C <sub>NC(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		32		pF
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room		78		1



Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, $\pm$ 10 %, V <sub>IN</sub> = 0.5 or 1.5 V <sup>e</sup>		Limits - 40 to 85 °C			
			Temp <sup>a</sup>	Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	Unit
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	۷
On-Resistance	r <sub>ON</sub>	V+ = 2.7 V, V <sub>COM</sub> = 0.2 V/1.5 V I <sub>NO</sub> , I <sub>NC</sub> = 100 mA	Room Full		0.85	1.2 1.3	Ω
r <sub>ON</sub> Flatness	r <sub>ON</sub> Flatness	V+ = 2.7 V, V <sub>COM</sub> = 0 to V+, I <sub>NO</sub> , I <sub>NC</sub> = 100 mA	Room			0.2	
r <sub>ON</sub> MatchFlat	$\Delta r_{ON}$		Room			0.06	
Switch Off Leakage Current	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 3.3 V V <sub>NO</sub> , V <sub>NC</sub> = 0.3 V/3 V, V <sub>COM</sub> = 3 V/10.3 V	Room Full	- 1 - 10		1 10	nA
Switch On Leakage Ourent	I <sub>COM(off)</sub>		Room Full	- 1 - 10		1 10	
Channel-On Leakage Current	I <sub>COM(on)</sub>	V+ = 3.3 V, V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 0.3 V/3 V	Room Full	- 1 - 10		1 10	
Digital Control							-
Input High Voltage	V <sub>INH</sub>		Full	1.5			v
Input Low Voltage	V <sub>INL</sub>		Full			0.5	v
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		3.3		pF
Input Current <sup>f</sup>	$I_{\rm INL}$ or $I_{\rm INH}$	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time	t <sub>ON</sub>	$V_{NO}$ or $V_{NC}$ = 2.0 V, $R_L$ = 300 $\Omega,C_L$ = 35 pF Figures 1 and 2	Room Full		28	51 55	- ns
Turn-Off Time	t <sub>OFF</sub>		Room Full		12	33 34	
Break-Before-Make Time	t <sub>d</sub>		Room	1			
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$ , Figure 3	Room		9		рС
Off-Isolation <sup>d</sup>	OIRR	$R_L$ = 50 Ω, $C_L$ = 5 pF, f = 1 MHz	Room		- 64		٩D
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 64		dB
NO, NC Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub> C <sub>NC(off)</sub>	$V_{IN} = 0$ or V+, f = 1 MHz	Room		30		pF
Channel-On Capacitance <sup>d</sup>	C <sub>ON</sub>		Room		77		
Power Supply	·	·	·		·		
Power Supply Range	V+			1.5		3.6	V
Power Supply Current	l+	$V$ + = 3.6 V, $V_{IN}$ = 0 or V+			0.01	1.0	μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

e.  $V_{IN}$  = input voltage to perform proper function.

f. Guaranteed by 3 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





 $r_{ON}$  vs.  $V_{COM}$  and Single Supply Voltage







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Supply Current vs. Input Switching Frequency





### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





## DG2714

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t<sub>r</sub> < 5 ns

t<sub>f</sub> < 5 ns

t<sub>D</sub>

### **TEST CIRCUITS**





Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.



Logic

Input

Switch

Output

VINH

V<sub>INL</sub>

 $V_{O}$ 

0 V

90 %

t<sub>D</sub>

 $V_{NC} = V_{NO}$ 



C<sub>L</sub> (includes fixture and stray capacitance)





Figure 3. Charge Injection



### **TEST CIRCUITS**





Figure 5. Channel Off/On Capacitance

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